

**AMENDMENTS TO THE SPECIFICATION:**

Please replace paragraph [0005] with the following amended paragraph:

[0005] As prior solid-state image sensing devices, therefore, a device, in which two integrating circuits are provided and the imaging operation is performed on all the pixels at the same timing, is suggested (see U.S. Publication of Patent Application No. ~~2002-77733~~ 2002/0054389). A structure of the pixels in the prior solid-state image sensing device is shown in Fig. 22. The pixel in Fig. 22 has a photoelectric conversion circuit 100, a capacitor C1, a capacitor C2, an MOS transistor T4, an MOS transistor T5, an MOS transistor T6, and an MOS transistor T3. The photoelectric conversion circuit 100 generates an electric signal according to incident light, and the capacitor C1 integrates the electric signal. The capacitor C2 samples and holds the electric signal integrated by the capacitor C1, and the MOS transistor T4 amplifies a current of the electric signal sampled and held by the capacitor C2. The MOS transistor T5 electrically connects and disconnects the capacitors C1 and C2, and the MOS transistor T6 serves as a switch for resetting the capacitor C2. The MOS transistor T3 serves as a switch for outputting the electric signal from the MOS transistor T4 as an image signal.